



**PATENT APPLICATION**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of

Docket No: Q61743

Takashi UDAGAWA

Appln. No.: 09/885,943 ✓

Group Art Unit: 2826 ✓

Confirmation No.: 6215

Examiner: Johannes P. MONDT

Filed: June 22, 2001

For: GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DEVICE AND  
PRODUCTION METHOD THEREOF

**AMENDMENT UNDER 37 C.F.R. § 1.111**

**MAIL STOP NON-FEE AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

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JUL 24 2003  
TECHNOLOGY CENTER 2800

Sir:

This Amendment is submitted in response to the Office Action dated April 23, 2003.

Please amend the above-identified application as follows:

**IN THE CLAIMS:**

**Please enter the following amended claim:**

1. (Three Times Amended) A group-III nitride semiconductor light-emitting device comprising a single crystal substrate having thereon a light-emitting part structure comprising a gallium nitride phosphide ( $\text{GaN}_{1-x}\text{P}_x$ , wherein  $0 < x < 1$ ) single crystal layer provided via a boron phosphide (BP)-based buffer layer, wherein

the boron phosphide-based buffer layer comprises a multilayer structure including an amorphous layer and a crystalline layer formed on the amorphous layer,